

DESCRIPTION

AMCOM's AM254540WM-BM/FM-R is part of the GaAs HiFET MMIC power amplifier series. This high efficiency MMIC is a 2-stage GaAs pHEMT power amplifier biased at 10 to 13V. The input and inter-stage matching networks cover 2.5 to 4.5GHz. This MMIC requires output external matching to your band of interest between 2.5GHz to 4.5GHz to provide maximum bandwidth flexibility. As an example, one of the available evaluation boards has over 17dB gain, 10 watts (40dBm) saturated output power over the 3.4 to 3.6GHz band at 12V.

This MMIC is in a ceramic package with both RF and DC leads at the lower level of the package to facilitate low-cost SMT assembly to the PC board. When mounting directly to PCB, please see application note AN700 for instructions. Because of high DC power dissipation, we strongly recommend to mount these devices directly on a metal heat sink. The AM254540WM-FM-R is the AM254540WM-BM-R mounted on a gold plated copper flange carrier. There are two screw holes on the flange to facilitate screwing on to a metal heat sink. This MMIC is RoHS compliant.

FEATURES

- Frequency applications from 2.5 to 4.5GHz
- High output power, P1dB = 38dBm
- High gain > 17dB
- Input matched from 2.5 to 4.5GHz
- High efficiency > 35%

APPLICATIONS

- WiMAX
- MMDS
- WLAN Repeaters
- 12V Applications

TYPICAL PERFORMANCE FOR 3.2 to 3.8 GHz TEST FIXTURE*

Performance at $V_{dd} = +12V$, $V_{gs} = -0.97V^{**}$, $I_{dq} = 1300mA$, $T_a = 25^{\circ}C$

Parameters	Minimum	Typical	Maximum
Frequency	3.4 – 3.6GHz	3.2 – 3.8GHz	
Small Signal Gain	15dB	17dB	
Gain Ripple		± 1.0dB	± 2.0dB
P1dB	37dBm	38dBm	
Psat		39dBm	
IP3		45dBm	
Efficiency @ P1dB		35%	
Input Return Loss	8dB	10dB	
Output Return Loss		5dB	
Thermal Resistance		5°C/W	

* Specifications subject to change without notice.

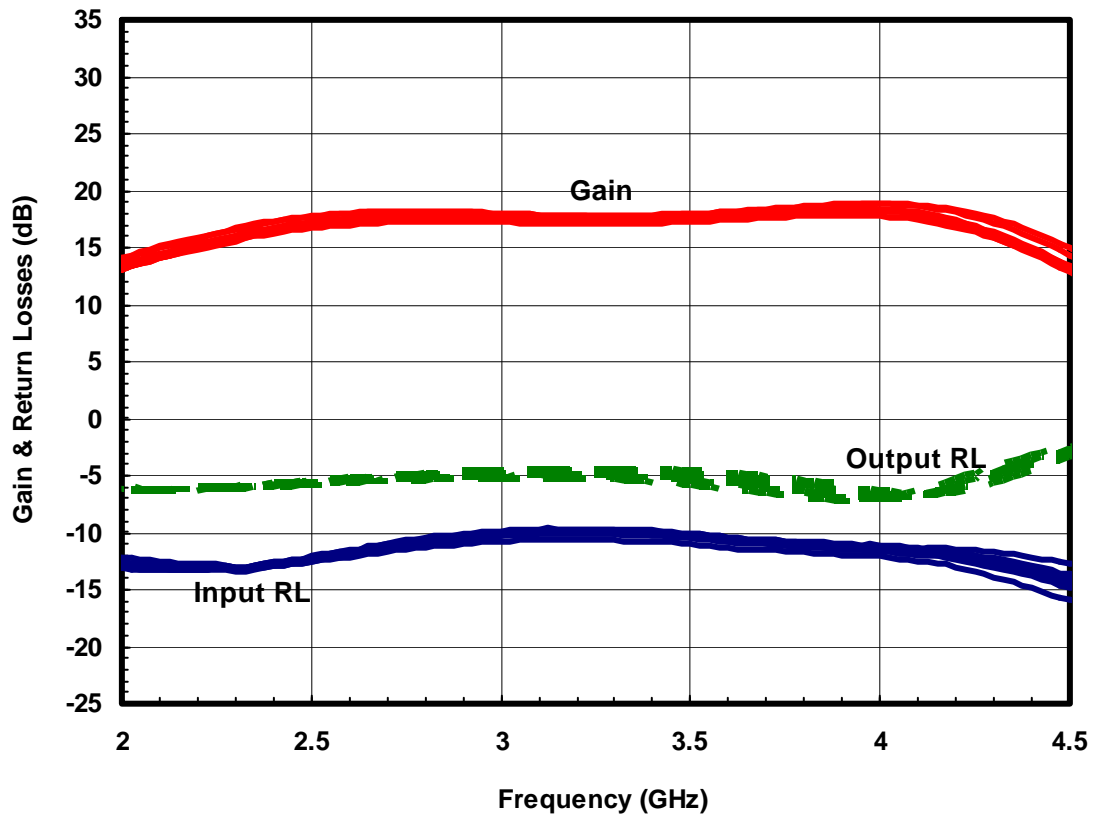
** V_{gs} may vary from lot to lot

ABSOLUTE MAXIMUM RATING

Parameters	Symbol	Rating
Drain source voltage	V_{dd}	13V
Gate source voltage	V_{gs}	-3V
Drain source current	I_{dd}	1.5A
Continuous dissipation at room temperature	P_t	25W
Channel temperature	T_{ch}	175°C
Storage temperature	T_{sto}	-55°C to +135°C

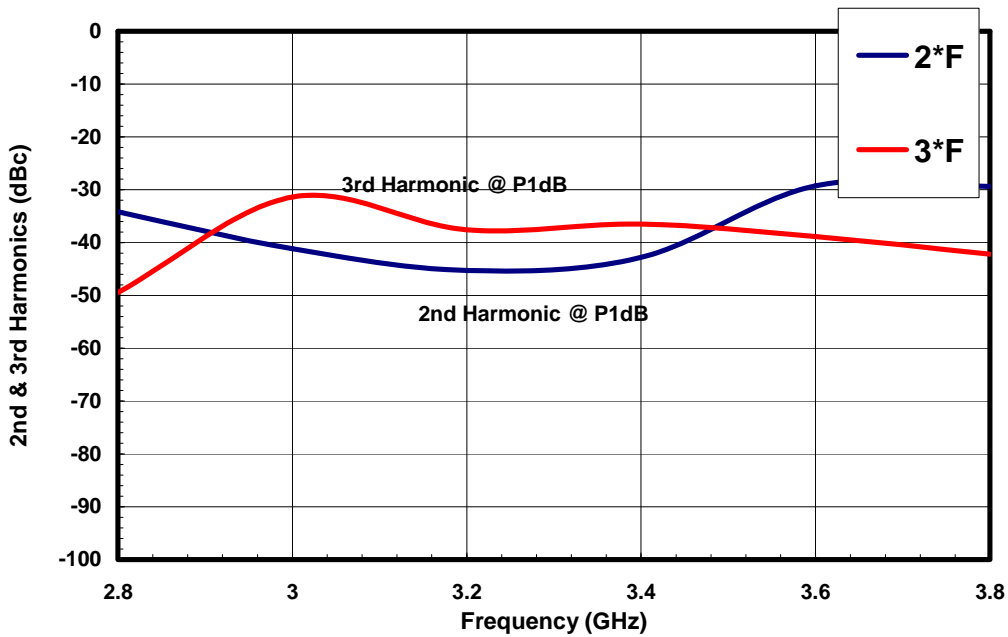
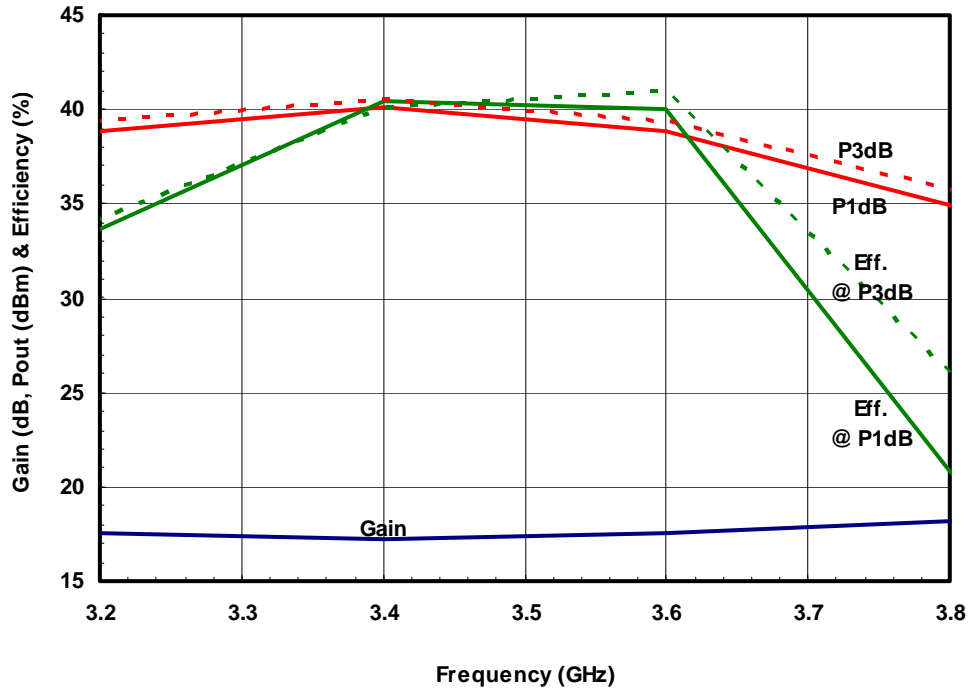
SMALL SIGNAL DATA

3.2 – 3.8GHz Matching Circuit
MMIC Bias: $V_{dd}=+12V$, $I_{dd}= 1.3A$, $V_{gs}=-0.97V$

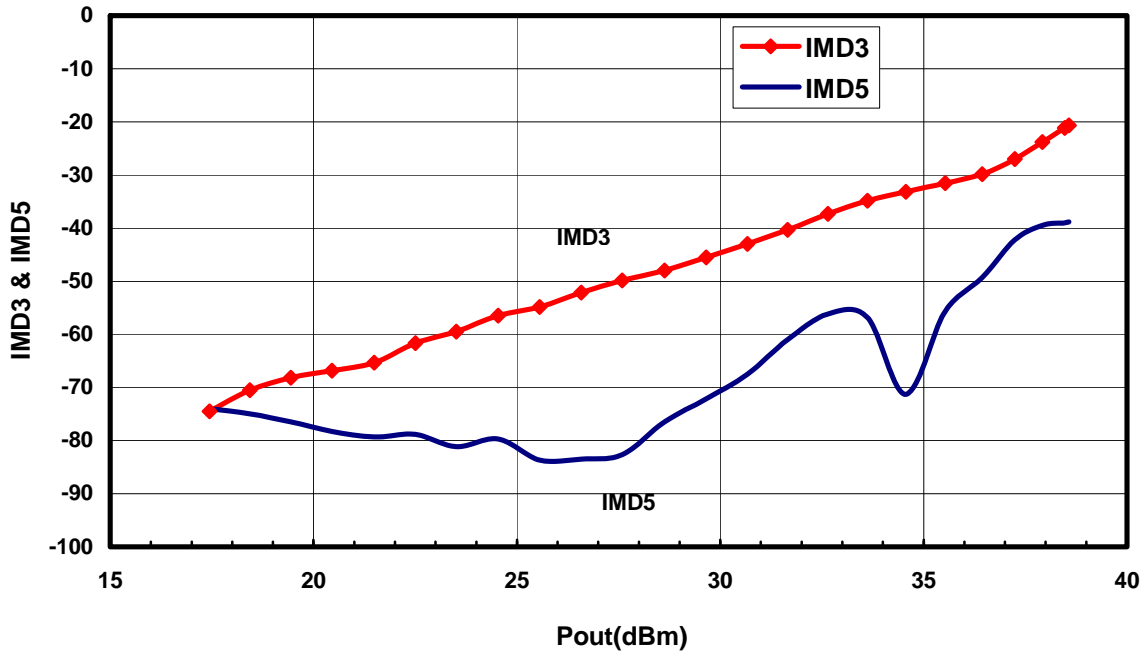


POWER DATA of 3.2 to 3.8GHz TEST BOARD

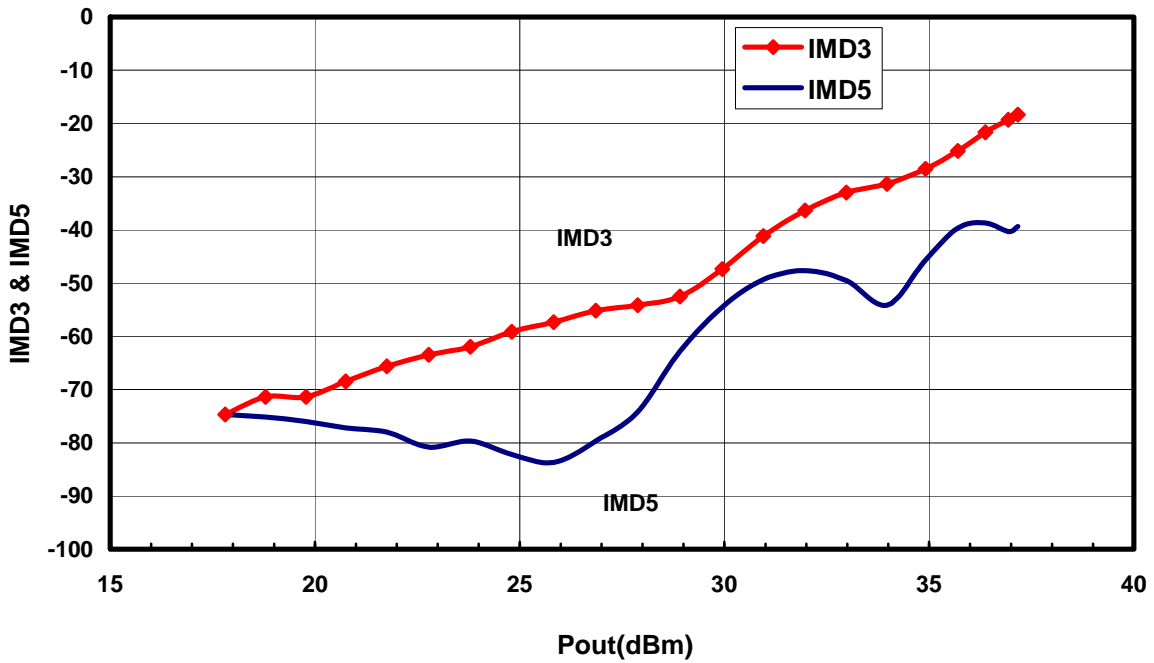
$V_{dd}=+12V, I_{dd1}=0.3A, I_{dd2}=1.0A$



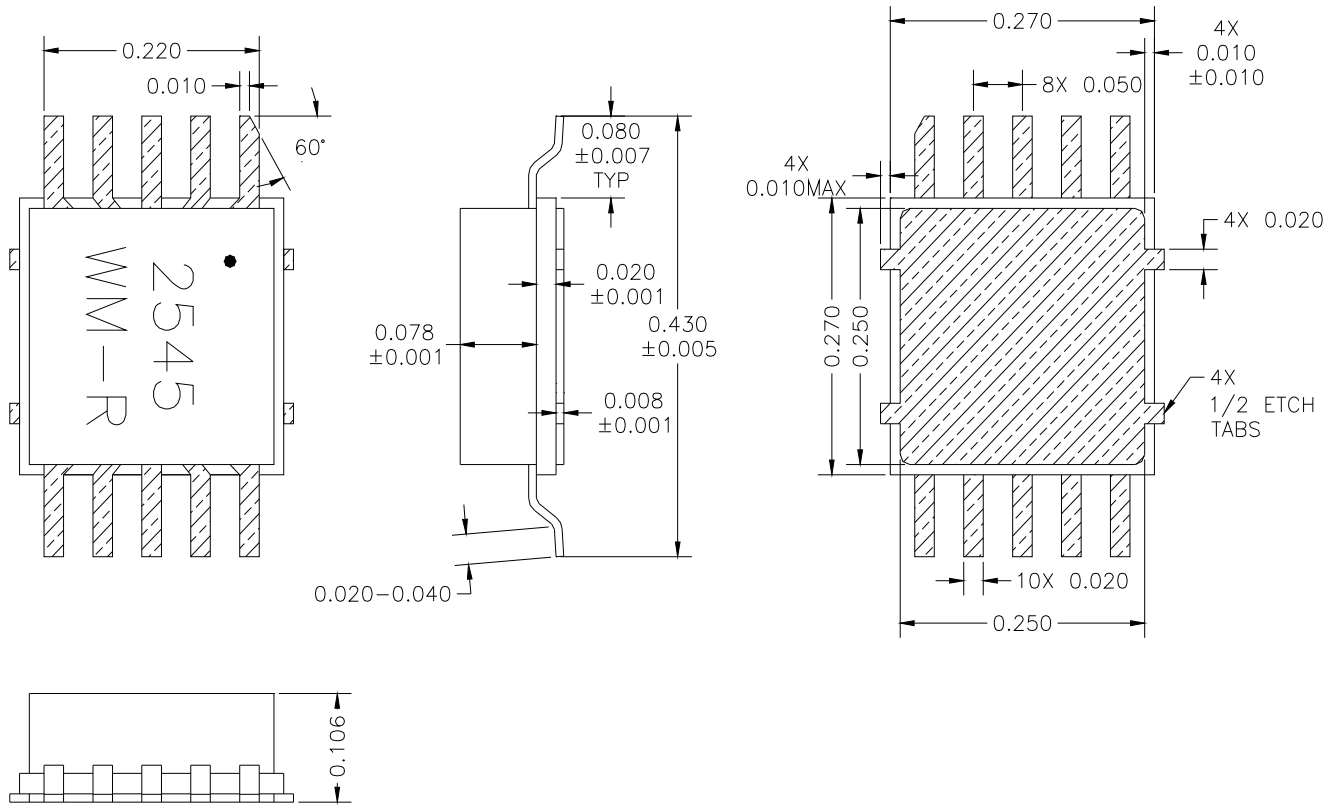
3.4GHz



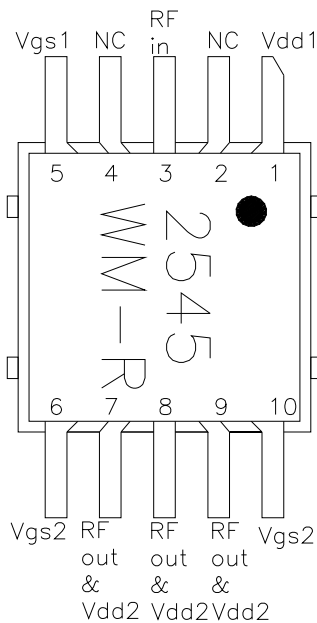
3.6GHz



PACKAGE OUTLINE (BM)



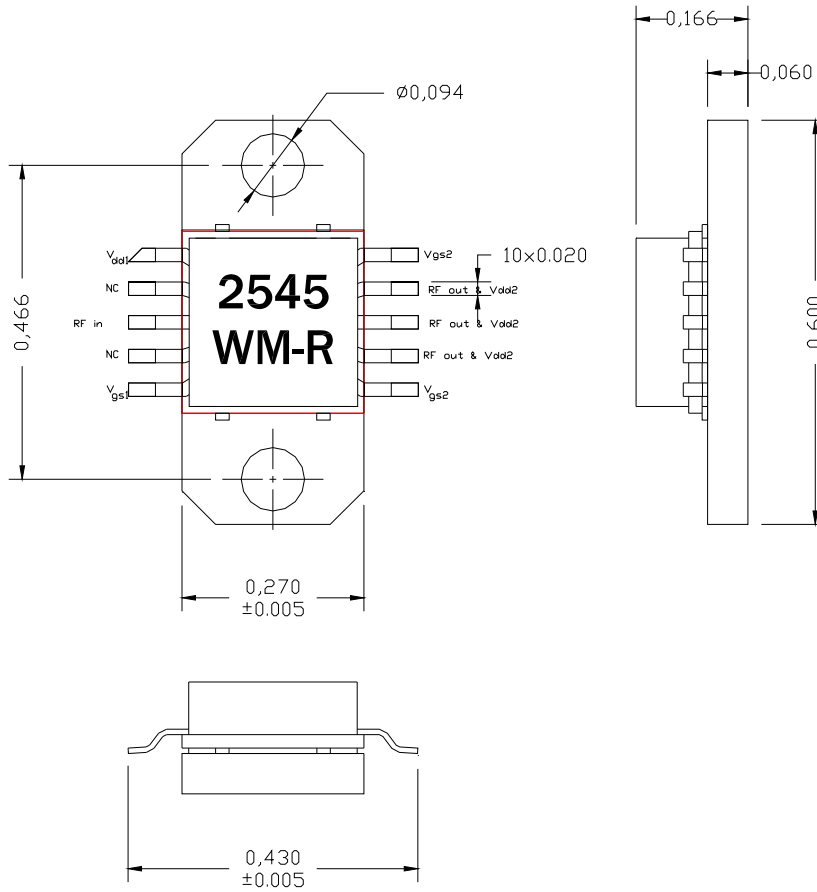
PIN LAYOUT



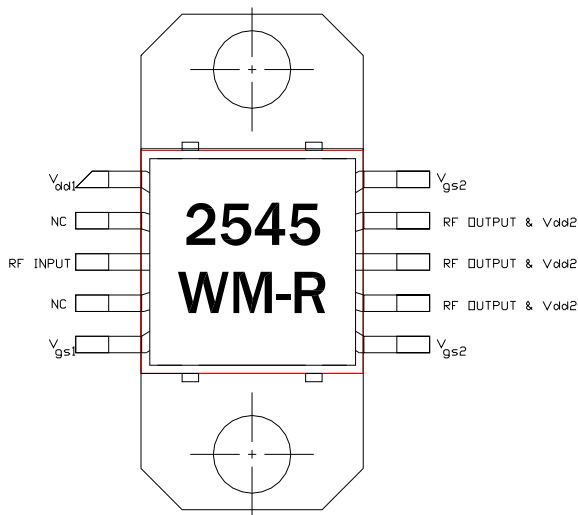
Pin No.	Function	Bias*
1	Vdd1	+12V
2	NC	
3	RF in	
4	NC	
5	Vgs1	-0.97V
6	Vgs2	-0.97V
7	RF out & Vdd2	+12V
8	RF out & Vdd2	+12V
9	RF out & Vdd2	+12V
10	Vgs2	-0.97V

* V_{gs1} , V_{gs2} may vary from lot to lot

PACKAGE OUTLINE (FM)



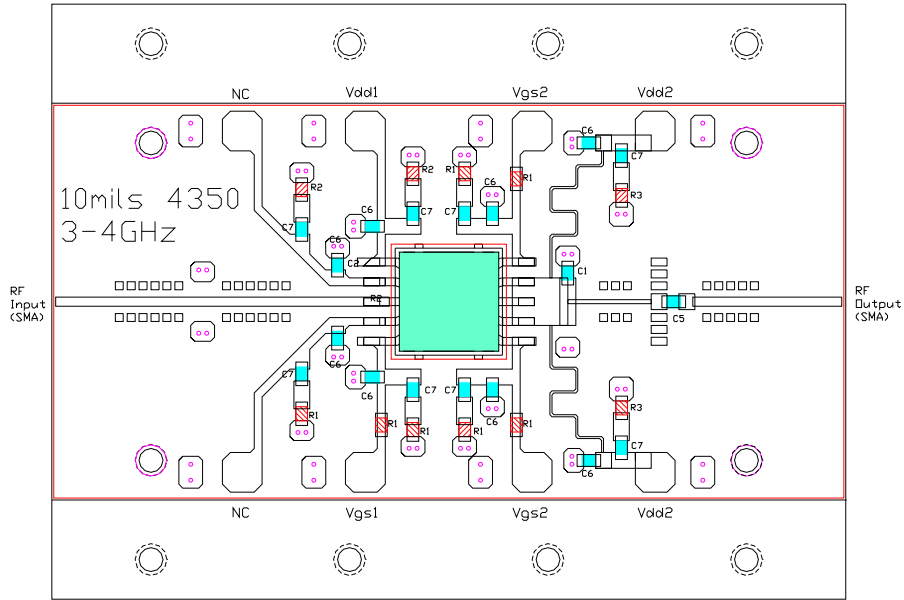
PIN LAYOUT



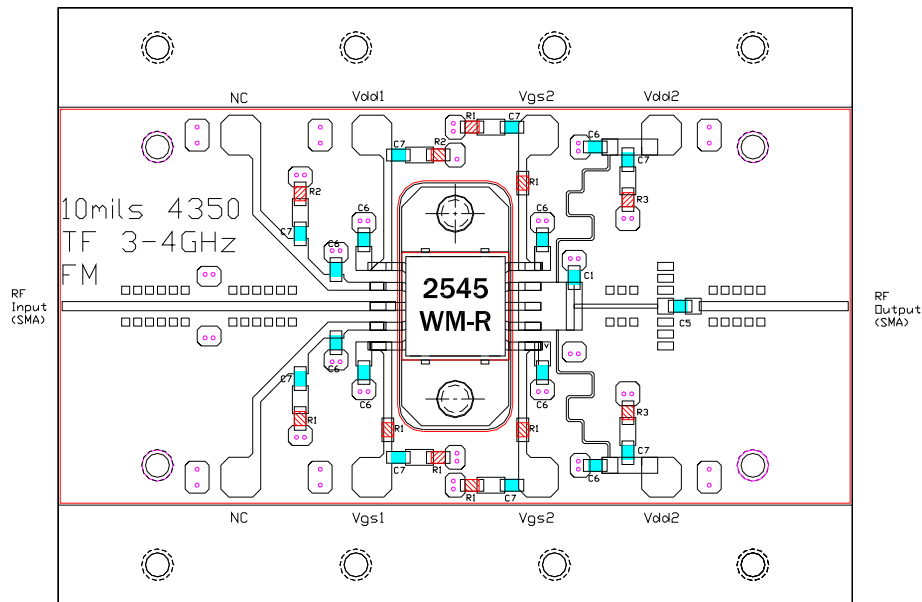
Pin No.	Function	Bias*
1	Vdd1	+12V
2	NC	
3	RF in	
4	NC	
5	Vgs1	-0.97V
6	Vgs2	-0.97V
7	RF out & Vdd2	+12V
8	RF out & Vdd2	+12V
9	RF out & Vdd2	+12V
10	Vgs2	-0.97V

* V_{gs1}, V_{gs2} may vary from lot to lot

3.2 to 3.8GHz TEST CIRCUITS



- Notes:
- 1- 10mils Rogers 4350 Material epoxied
 - 2- Ckt is for un-matched MMICs
 - 3- C1=0.5pF, C5=10.0pF, C6=20pF, C7=1000pF, R1=50ohms, R2=10ohms, R3=50ohms
 - 4- All Caps & Resistors are 0603 size
 - 5- External 1 μ F dipped tantalum capacitor should be attached to Vd and Vg to decouple external bias leads.



- Notes:
- 1- 10mils Rogers 4350 Material epoxied
 - 2- Ckt is for 3-4GHz un-matched MMICs
 - 3- C1=0.5pF, C5=10.0pF, C6=20pF, C7=1000pF, R1=50ohms, R2=10ohms, R3=50ohms
 - 4- All Caps & Resistors are 0603 size
 - 5- External 1 μ F dipped tantalum capacitor should be attached to Vd and Vg to decouple external bias leads.